

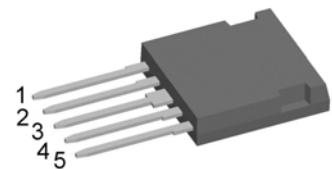
## Standard Rectifier

1~ Rectifier
$V_{RRM} = 1200 \text{ V}$
$I_{DAV} = 20 \text{ A}$
$I_{FSM} = 150 \text{ A}$

### 1~ Rectifier Bridge

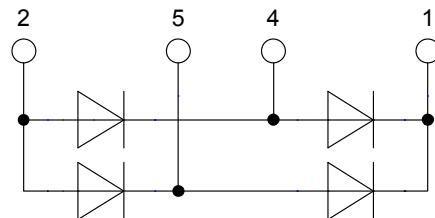
Part number

FBO16-12N



Backside: isolated

E72873



#### Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very low forward voltage drop
- Improved thermal behaviour

#### Applications:

- Diode Bridge for main rectification

#### Package: i4-Pac

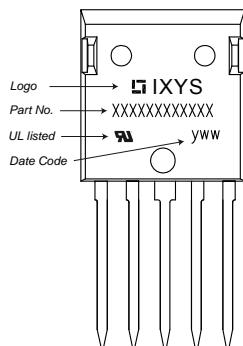
- Isolation Voltage: 3000 V~
- Industry convenient outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Soldering pins for PCB mounting
- Backside: DCB ceramic
- Reduced weight
- Advanced power cycling

## Rectifier

Symbol	Definition	Conditions	Ratings			
			min.	typ.	max.	
$V_{RSM}$	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^\circ C$			1300	V
$V_{RRM}$	max. repetitive reverse blocking voltage	$T_{VJ} = 25^\circ C$			1200	V
$I_R$	reverse current, drain current	$V_R = 1200 V$ $V_R = 1200 V$	$T_{VJ} = 25^\circ C$ $T_{VJ} = 150^\circ C$		10 1	$\mu A$ mA
$V_F$	forward voltage drop	$I_F = 10 A$ $I_F = 20 A$ $I_F = 10 A$ $I_F = 20 A$	$T_{VJ} = 25^\circ C$ $T_{VJ} = 150^\circ C$		1.21 1.43 1.14 1.45	V V V V
$I_{DAV}$	bridge output current	$T_C = 130^\circ C$ rectangular $d = 0.5$	$T_{VJ} = 175^\circ C$		20	A
$V_{FO}$ $r_F$	threshold voltage slope resistance } for power loss calculation only		$T_{VJ} = 175^\circ C$		0.81 32	V $m\Omega$
$R_{thJC}$	thermal resistance junction to case				3	K/W
$R_{thCH}$	thermal resistance case to heatsink			0.20		K/W
$P_{tot}$	total power dissipation		$T_C = 25^\circ C$		50	W
$I_{FSM}$	max. forward surge current	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$ $t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$ $t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$ $t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$	$T_{VJ} = 45^\circ C$ $V_R = 0 V$ $T_{VJ} = 150^\circ C$ $V_R = 0 V$		150 160 130 140	A
$I^2t$	value for fusing	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$ $t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$ $t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$ $t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$	$T_{VJ} = 45^\circ C$ $V_R = 0 V$ $T_{VJ} = 150^\circ C$ $V_R = 0 V$		115 105 85 82	$A^2s$ $A^2s$ $A^2s$ $A^2s$
$C_J$	junction capacitance	$V_R = 400 V; f = 1 \text{ MHz}$	$T_{VJ} = 25^\circ C$		4	pF

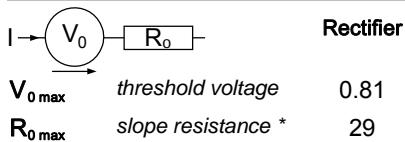
Package i4-Pac			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$I_{RMS}$	RMS current	per terminal			35	A
$T_{stg}$	storage temperature		-55		150	°C
$T_{VJ}$	virtual junction temperature		-55		175	°C
<b>Weight</b>				9		g
$F_c$	mounting force with clip		20		120	N
$d_{Spp/App}$	creepage distance on surface   striking distance through air	terminal to terminal	1.7			mm
$d_{Spb/Apb}$		terminal to backside	5.1			mm
$V_{ISOL}$	isolation voltage	t = 1 second t = 1 minute	3000 50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA	2500		V

## Product Marking



Ordering	Part Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	FBO16-12N	FBO16-12N	Tube	25	492310

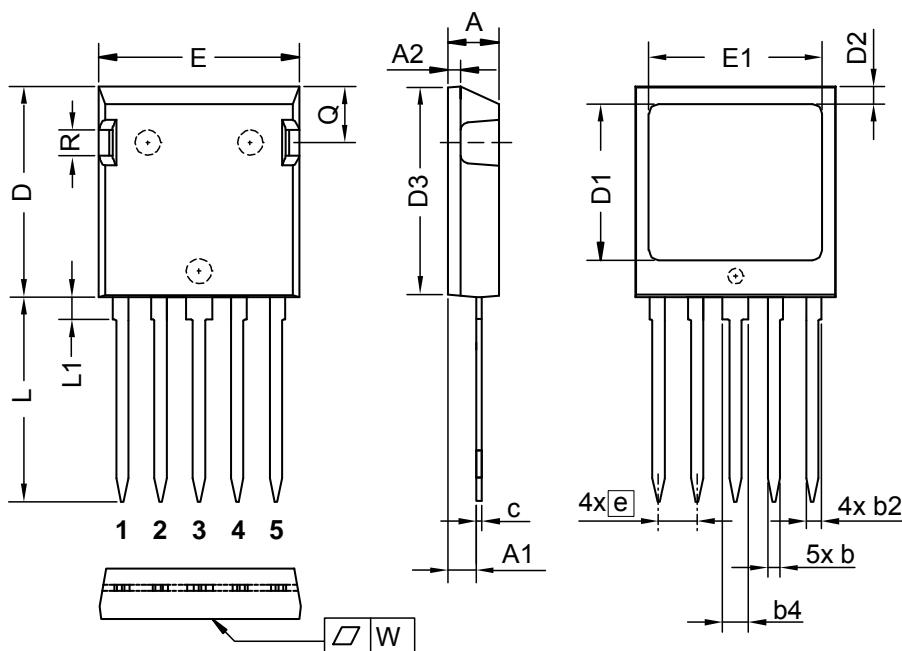
## Equivalent Circuits for Simulation

<sup>\*</sup> on die level $T_{VJ} = 175$  °C

$V_{0\max}$  threshold voltage 0.81  
 $R_{0\max}$  slope resistance \* 29

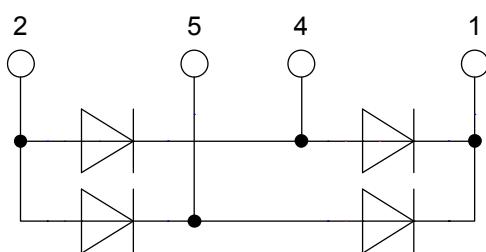
V  
 mΩ

## Outlines i4-Pac



Dim.	Millimeter		Inches	
	min	max	min	max
A	4.83	5.21	0.190	0.205
A1	2.59	3.00	0.102	0.118
A2	1.17	2.16	0.046	0.085
b	1.14	1.40	0.045	0.055
b2	1.47	1.73	0.058	0.068
b4	2.54	2.79	0.100	0.110
c	0.51	0.74	0.020	0.029
D	20.80	21.34	0.819	0.840
D1	14.99	15.75	0.590	0.620
D2	1.65	2.03	0.065	0.080
D3	20.30	20.70	0.799	0.815
E	19.56	20.29	0.770	0.799
E1	16.76	17.53	0.660	0.690
e	3.81	BSC	0.150	BSC
L	19.81	21.34	0.780	0.840
L1	2.11	2.59	0.083	0.102
Q	5.33	6.20	0.210	0.244
R	2.54	4.57	0.100	0.180
W	-	0.10	-	0.004

Die konvexe Form des Substrates ist typ. < 0.05 mm über der Kunststoffoberfläche der Bauteilunterseite  
The convexbow of substrate is typ. < 0.05 mm over plastic surface level ofdevice bottom side



## Rectifier

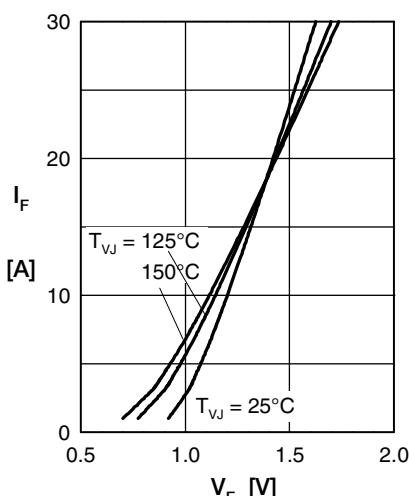


Fig. 1 Forward current versus voltage drop per diode

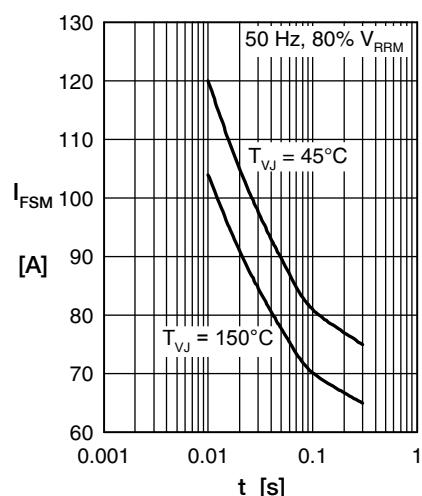


Fig. 2 Surge overload current

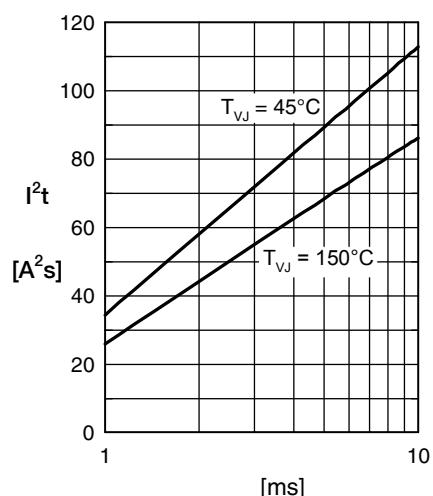
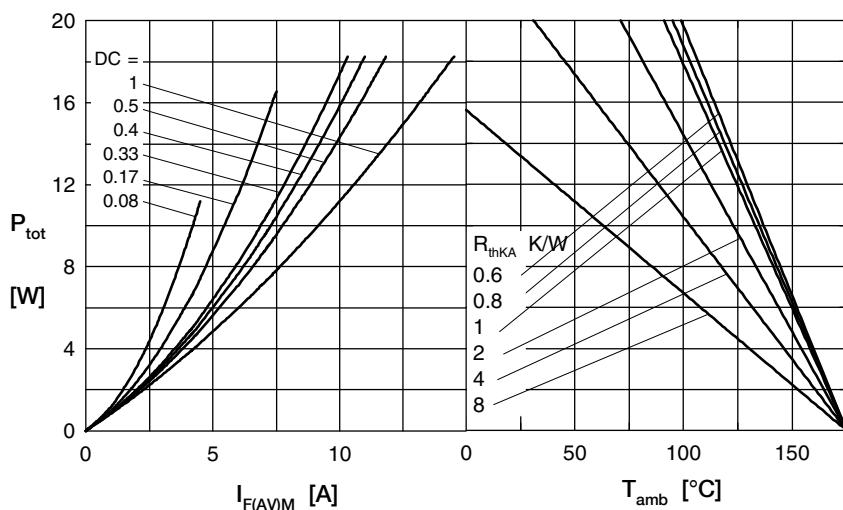
Fig. 3  $I^2t$  versus time per diode

Fig. 4 Power dissipation vs. direct output current &amp; ambient temperature

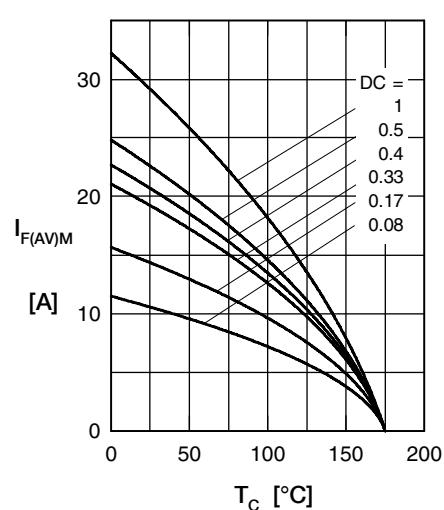


Fig. 5 Max. forward current vs. case temperature

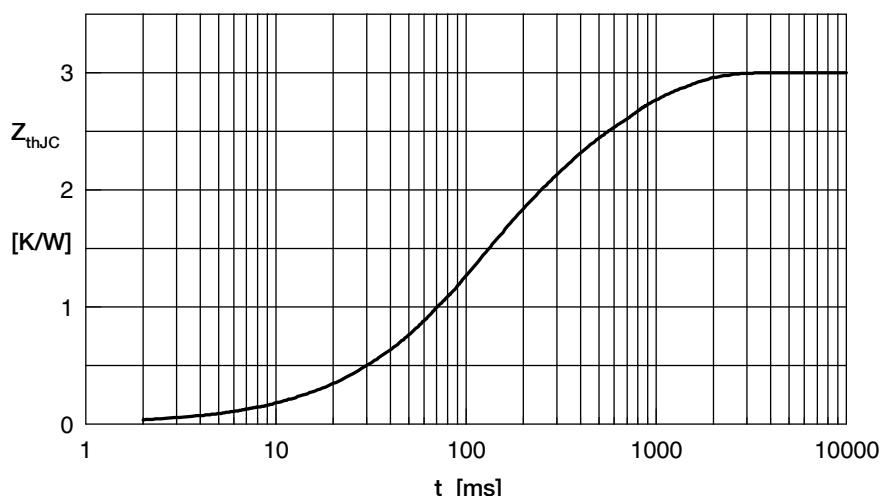


Fig. 6 Transient thermal impedance junction to case

Constants for  $Z_{thJC}$  calculation:

i	$R_{thi}$ (K/W)	$t_i$ (s)
1	1.359	0.1015
2	0.3286	0.1026
3	0.4651	0.4919
4	0.8473	0.62